

LBTP180Y3T1G

S-LBTP180Y3T1G

PNP medium power transistors

1. FEATURES

- High current
- Low voltage
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. APPLICATIONS

- Medium power general purposes.
- Driver stages of audio amplifiers.

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBTP180Y3T1G	E	1000/Tape&Reel

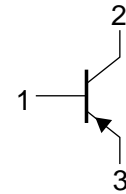
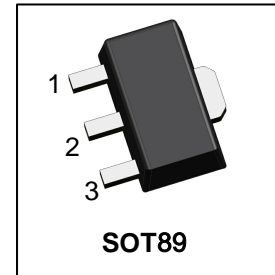
4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	VCEO	-80	V
Collector–Base Voltage	VCBO	-100	V
Emitter–Base Voltage	VEBO	-5	V
Collector Current(DC)	IC	-1	A
Peak collector current	ICM	-1.5	A
Peak base current	IBM	-200	mA

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	550 4.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient	RθJA	225	°C/W
Junction–to–Case	RθJC	50	°C/W
Junction and Storage temperature	TJ, Tstg	-65~+150	°C

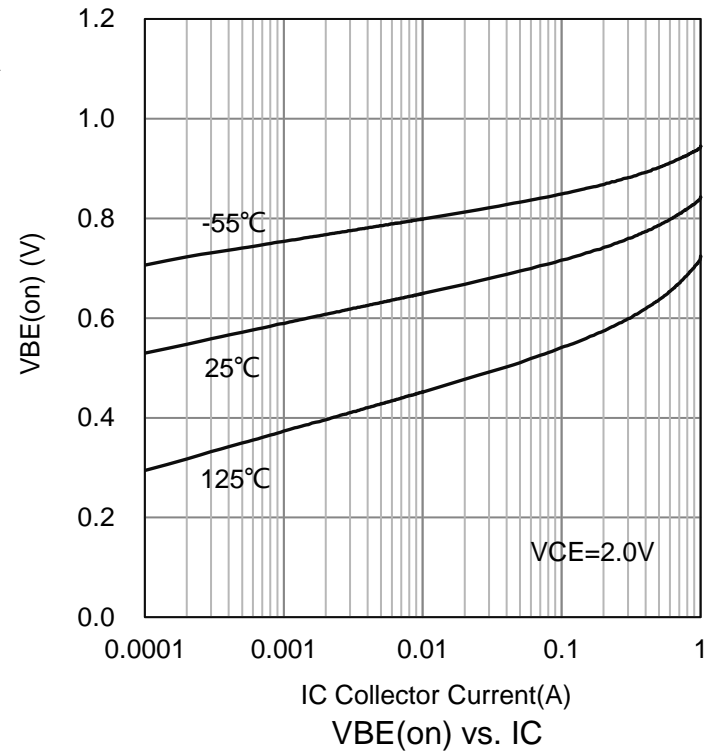
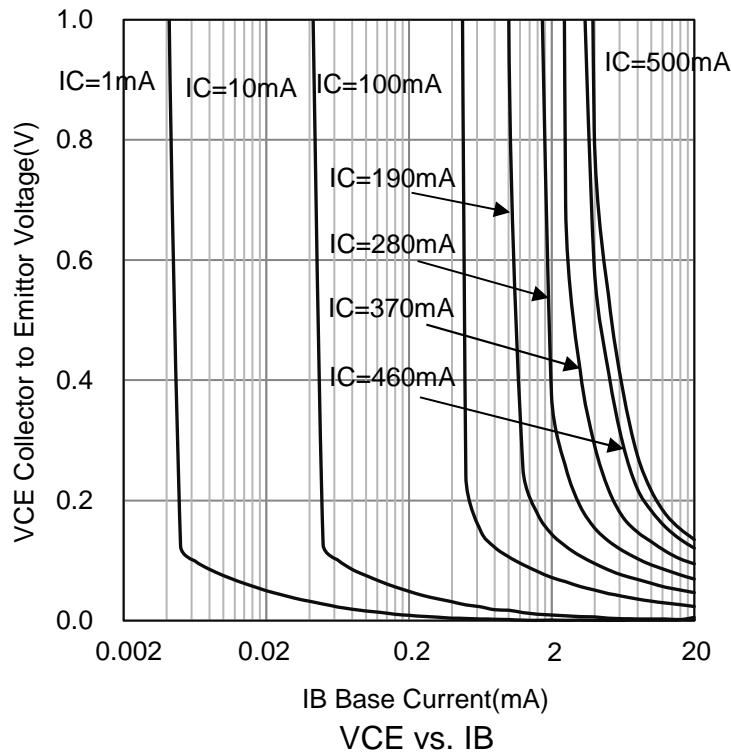
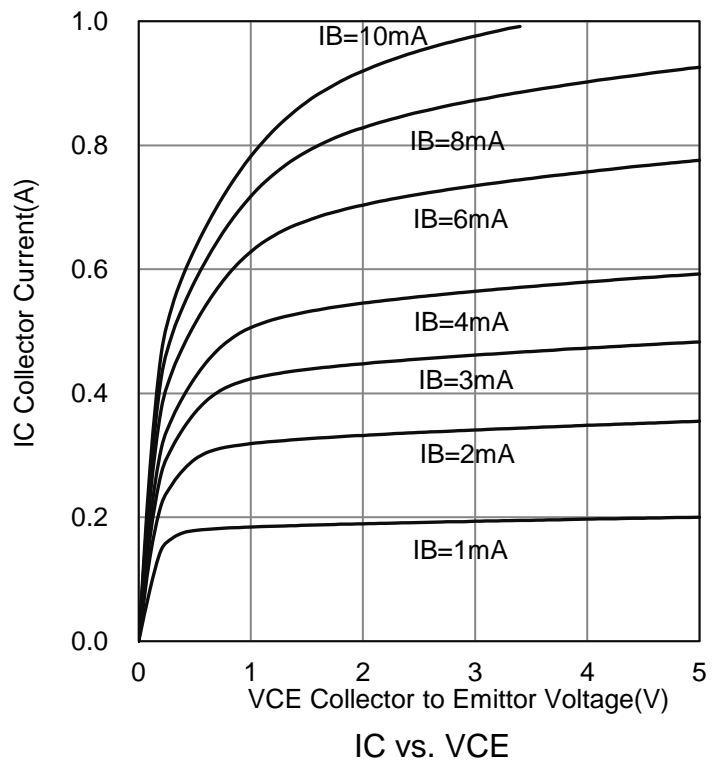
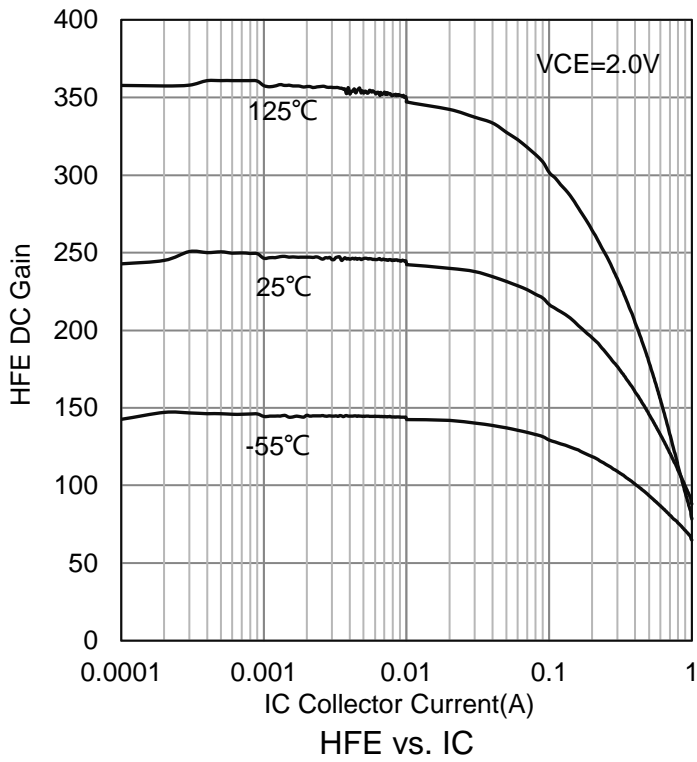
1. PCB Size:30.0mm×25.0mm×1.6mm,FR-4 Board;



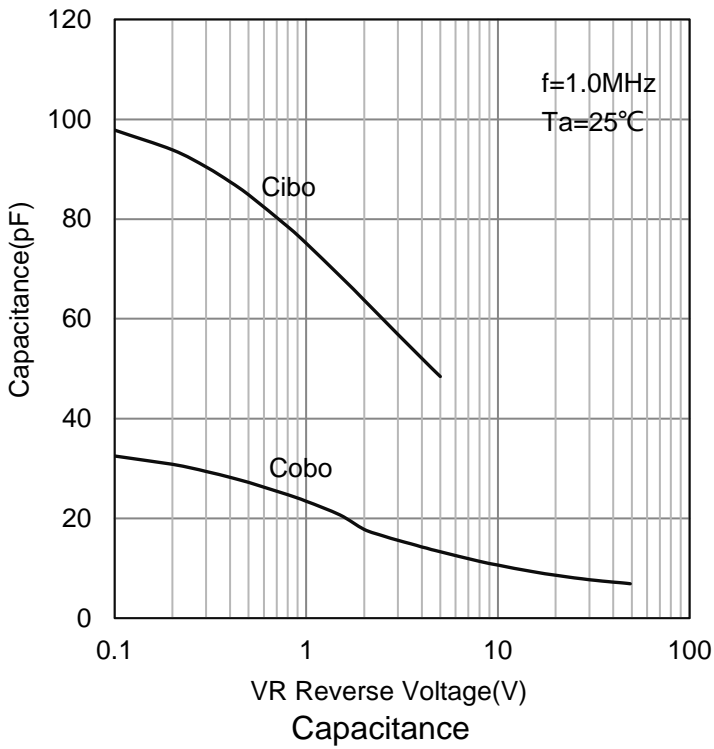
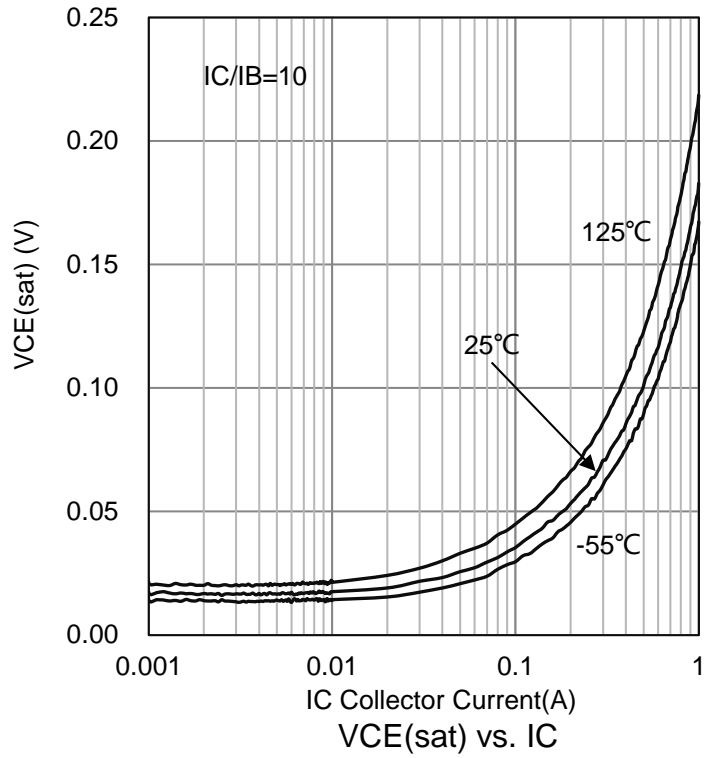
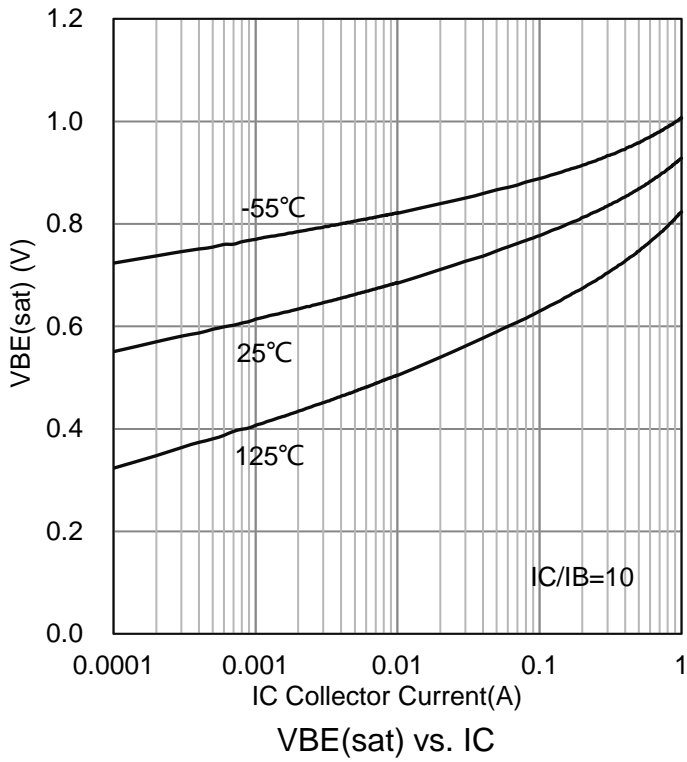
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = -1 mA, IB = 0)	VBR(CEO)	-80	-	-	V
Collector–Base Breakdown Voltage (IC = -100 μA, IE = 0)	VBR(CBO)	-100	-	-	V
Emitter–Base Breakdown Voltage (IE = -100 μA, IC = 0)	VBR(EBO)	-5	-	-	V
Collector Cutoff Current (VCB = -30 V, IE = 0) (VCB = -30 V, IE = 0, Tj = 125 °C)	ICBO	-	-	-100 -10	nA μA
Emitter Cut-off Current (VEB = -5V, IC = 0)	IEBO	-	-	-100	nA
Collector-Emitter cutoff Current (VCE = -80V, IB = 0)	ICEO	-	-	-10	μA
DC Current Gain (VCE = -2V, IC = -5mA) (VCE = -2V, IC = -150mA) (VCE = -2V, IC = -500mA)	HFE	40 100 45	- - -	- 250 -	
Collector–Emitter Saturation Voltage (IC = -500 mA, IB = -50 mA)	VCE(sat)	-	-	-500	mV
Base-emitter voltage (IC = -500 mA, VCE = -2 V)	VBE	-	-	-1	V
Transition Frequency (IC = -10 mA, VCE = -5 V, f = 100 MHz)	fT	-	50	-	MHz

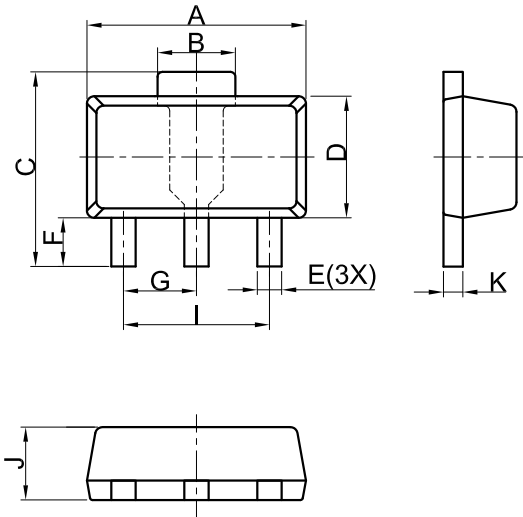
7.ELECTRICAL CHARACTERISTICS CURVES



7.ELECTRICAL CHARACTERISTICS CURVES(Con.)



8.OUTLINE AND DIMENSIONS

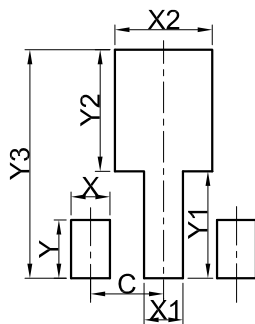


SOT89			
DIM	MIN	NOR	MAX
A	4.30	4.50	4.70
B	1.40	1.60	1.80
C	3.90	4.00	4.25
D	2.30	2.50	2.70
E	0.40	0.50	0.58
F	0.90	1.00	1.20
G	1.50 BSC		
I	3.00 BSC		
J	1.40	1.50	1.60
K	0.34	0.40	0.50
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um
4. Protrusion or Gate Burrs shall not exceed 0.10mm per side.

9.SOLDERING FOOTPRINT



SOT89	
DIM	(mm)
X	0.80
Y	1.20
X1	0.80
Y1	2.20
X2	2.00
Y2	2.50
C	1.50
Y3	4.70

DISCLAIMER

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